

Mid-term assessment test of Condensed Matter Physics - January 14th 2020
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Exercise 1: Tight binding.

Consider the two-dimensional centered rectangular Bravais lattice shown in Fig. 1. Each lattice site hosts an atom with one valence electron, occupying an s -type orbital, whose wave function $\phi_s(\mathbf{r})$ is real. The lattice parameters of the conventional unit cell (highlighted in Fig. 1) are $a = 0.15$ nm and $b = 0.20$ nm.

1. Neglecting all overlap integrals, write the expression of the energy band dispersion $E(k_x, k_y)$ in the tight-binding approximation, considering the contributions from the first, second, and third neighbours only (for the site 0, taken as the origin, these are indicated in Fig. 1 by the labels 1, 2, and 3, respectively). The values of the transfer integrals $\gamma_i \equiv \gamma(\mathbf{R}_i) = -\int d\mathbf{r} \phi_s(\mathbf{r}) \Delta U(\mathbf{r}) \phi_s(\mathbf{r} - \mathbf{R}_i)$ are $\gamma_1 = 0.75$ eV, $\gamma_2 = 0.25$ eV, and $\gamma_3 = 0.15$ eV, for the first, second, and third neighbours, respectively. Indicate with E_s the energy level of the atomic s orbital and let $\beta = \gamma(\mathbf{R} = 0)$. [The numerical values of these two parameters are not needed to answer the following question].

2. Evaluate the elements of the electron effective mass tensor, m_{xx} , m_{yy} , and $m_{xy} = m_{yx}$ (in kg) at the Γ point of the first Brillouin zone ($k_x = 0, k_y = 0$).

3. Determine the electron density n (in m^{-2}).

[Note that 1 eV corresponds to an energy of 1.60×10^{-19} J, and the Planck constant is $\hbar = 1.05 \times 10^{-34}$ J·s. The free electron mass is $m_0 = 9.11 \times 10^{-31}$ kg].

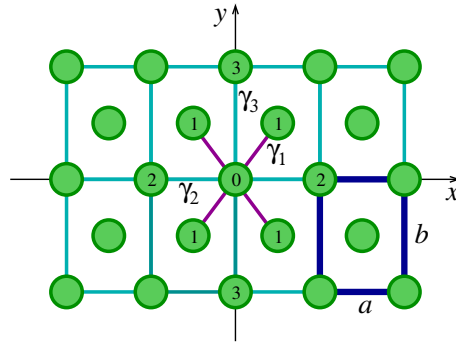


Fig. 1.

Exercise 2: Semiconductors.

Consider an intrinsic semiconductor that can be described as a two band system, with effective mass of the electrons in the conduction band $m_c = 0.2 m_0$ and effective mass of the holes in the valence band $m_v = 0.5 m_0$, where $m_0 = 9.11 \times 10^{-31}$ kg is the free electron mass.

1. Knowing that the density of intrinsic carriers at a temperature $T = 300$ K is $n_i = 7 \times 10^{17} \text{ m}^{-3}$, determine the value of the band gap E_g (in eV).

2. Assuming the origin of the energies at the top of the valence band, ε_v , so that $\varepsilon_v = 0$ and the bottom of the conduction band is $\varepsilon_c = E_g$, determine the value of the chemical potential μ_i (in eV), at $T = 300$ K.

3. To increase the density of electrons in the conduction band, the semiconductor is doped with donors. Assuming that the donors are fully ionized at $T = 300$ K, determine the density of donors N_d that is needed to increase the density of electrons in the conduction band n_c by a factor 10^3 with respect to the intrinsic case considered before. What is now the density of holes in the valence band p_v ?

[Note that 1 eV corresponds to a temperature of 1.16×10^4 K or to an energy of 1.60×10^{-19} J, the Planck constant is $\hbar = 1.05 \times 10^{-34}$ J·s, and the Boltzmann constant is $\kappa_B = 1.38 \times 10^{-23}$ J·K⁻¹].

Solution of the mid-term assessment test
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Exercise 1.

1. We have

$$E(k_x, k_y) = E_s - \beta - \sum_{i=1,2,3} \sum_{\mathbf{R}_i} \gamma(\mathbf{R}_i) e^{i\mathbf{k}\cdot\mathbf{R}_i},$$

where $\mathbf{R}_1 = (\pm\frac{1}{2}a, \pm\frac{1}{2}b)$; $\mathbf{R}_2 = (\pm a, 0)$; $\mathbf{R}_3 = (0, \pm b)$; $\mathbf{k} = (k_x, k_y)$. Then

$$E(k_x, k_y) = E_s - \beta - 4\gamma_1 \cos\left(\frac{1}{2}k_x a\right) \cos\left(\frac{1}{2}k_y b\right) - 2\gamma_2 \cos(k_x a) - 2\gamma_3 \cos(k_y b).$$

2. Expanding near the Γ point we find

$$E(k_x, k_y) \approx E_s - \beta - 4\gamma_1 - 2\gamma_2 - 2\gamma_3 + \frac{1}{2}(\gamma_1 + 2\gamma_2)a^2 k_x^2 + \frac{1}{2}(\gamma_1 + 2\gamma_3)b^2 k_y^2,$$

hence the effective mass tensor is diagonal, $m_{xy} = m_{yx} = 0$, and

$$m_{xx} = \frac{\hbar^2}{(\gamma_1 + 2\gamma_2)a^2} = 2.47 \times 10^{-30} \text{ kg} = 2.71 m_0, \quad m_{yy} = \frac{\hbar^2}{(\gamma_1 + 2\gamma_3)b^2} = 1.65 \times 10^{-30} \text{ kg} = 1.81 m_0.$$

3. There are two atoms in the conventional unit cell, each contributing one electron, hence

$$n = \frac{2}{ab} = 6.67 \times 10^{19} \text{ m}^{-2}.$$

Exercise 2.

1. We have $\kappa_B T = 4.14 \times 10^{-21} \text{ J} = 2.58 \times 10^{-2} \text{ eV}$. Since

$$n_i = \frac{1}{4} \left(\frac{2\kappa_B T}{\pi \hbar^2} \right)^{3/2} (m_c m_v)^{3/4} e^{-E_g/2\kappa_B T},$$

we find

$$E_g = 2\kappa_B T \log \left[\frac{1}{4n_i} \left(\frac{2\kappa_B T}{\pi \hbar^2} \right)^{3/2} (m_c m_v)^{3/4} \right] = 0.812 \text{ eV}.$$

2. The chemical potential is

$$\mu_i = \frac{1}{2}E_g + \frac{3}{4}\kappa_B T \log \frac{m_v}{m_c} = 0.424 \text{ eV}.$$

3. If the donors are fully ionized

$$N_d \approx n_c = 10^3 n_i = 7 \times 10^{20} \text{ m}^{-3}.$$

Then, according to the law of mass action,

$$p_v = \frac{n_i^2}{n_c} = 10^{-3} n_i = 7 \times 10^{14} \text{ m}^{-3}$$

is reduced by a factor 10^3 with respect to the intrinsic case.